IN THE CLAIMS

1. ~~A metallization structure in~~ Aa multilayer stack comprising a dielectric layer and one or more surrounding dielectric layers situated above or below the dielectric layer, a dielectric constant of the dielectric layer being greater than a dielectric constant of the surrounding dielectric layers, and a metallization structure which is arranged on the dielectric layer and is arranged at a distance from a ground electrode, ~~characterized in that~~whereinwherein the metallization structure has a capacitor electrode ~~(22)~~ and a line ~~(24)~~ that acts as a coil, where the capacitor electrode ~~(22)~~ and the line ~~(24)~~ are arranged in a common plane which lies parallel to the ground electrode ~~(30)~~ at a distance h_1, and ~~in that~~ wherein $w/h_1 > 3$,where w is the width of the line (24)the metallization structure (20) is .

2. A metallization structure as claimed in claim 1, ~~characterized in that~~wherein a second ground electrode (32) is provided, the plane comprising capacitor electrode (22) and line (24) being arranged parallel to said second ground electrode at a distance h_2, and in that the plane comprising capacitor electrode (22) and line (24) lies between the first and second ground electrodes (30, 32), where $w/h_2 > 3$.

3. (Canceled)

4. (Cancel)

5. A multilayer stack as claimed in claim 3, ~~characterized in that~~wherein ~~the following~~

~~applies in respect of the layer thickness (d_{medium}) of the dielectric layer (14):~~

$$\frac{\varepsilon_{medium} \cdot d_{\varepsilon}}{\varepsilon \cdot d_{medium}} > 5$$

wherein the dielectric constant of and a thickness of the dielectric layer are ε_{medium} and d_{medium}, respectively, and the dielectric constant of and a thickness of the surrounding dielectric layers are ε and d_{ε}, respectively.

6. A multilayer stack as claimed in claim 3 comprising one or more additional metallization structures in the plane, ~~characterized in that~~wherein

$$\frac{\varepsilon_{medium} \cdot d_{min}}{\varepsilon \cdot d_{medium}} > 7 ,$$

where d_{min} is the minimum distance to ~~the next~~a nearest metallization structure in the plane.

7. A multilayer stack as claimed in claim 3, ~~characterized in that~~wherein ~~it~~ the multilayer stack comprises magnetic layers.

8. A multilayer stack as claimed in claim 3, produced in a multilayer laminate process.

9. A multilayer stack as claimed in claim 3, produced in an LTCC process.

10. (Canceled)